

# MA3X740

## Silicon epitaxial planar type

For super high speed switching circuit  
For small current rectification

### ■ Features

- Two MA3X721s are contained in one package (series connection)
- Allowing to rectify under ( $I_{F(AV)} = 200 \text{ mA}$ ) condition (single diode value)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Reverse voltage (DC)	$V_R$	30	V	
Repetitive peak reverse voltage	$V_{RRM}$	30	V	
Average forward current	Single	$I_{F(AV)}$	200	mA
	Double <sup>*1</sup>			
Peak forward current	Single	$I_{FM}$	300	mA
	Double <sup>*1</sup>			
Non-repetitive peak forward surge current <sup>*2</sup>	Single	$I_{FSM}$	1	A
	Double <sup>*1</sup>			
Junction temperature	$T_j$	150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$	

Note) \*1 : Value per chip

\*2 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

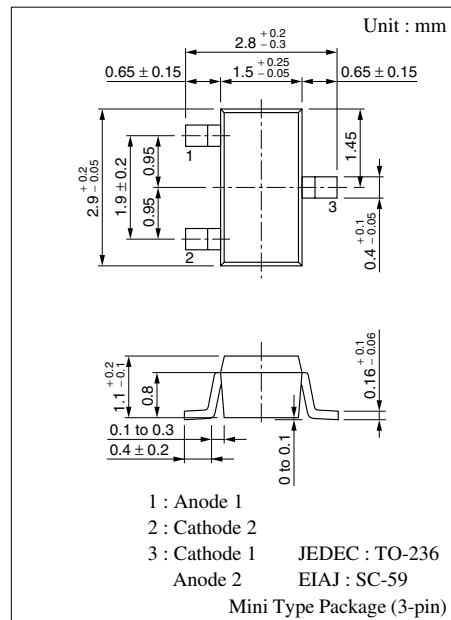
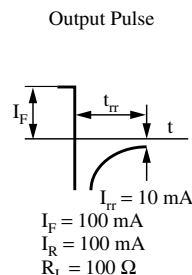
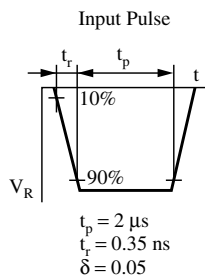
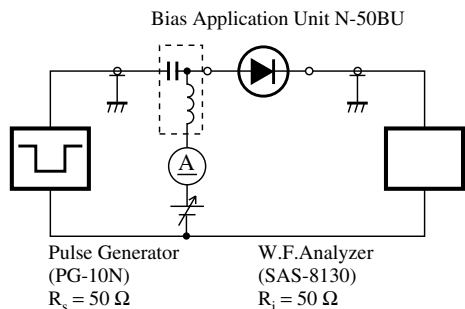
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 30 \text{ V}$			50	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 200 \text{ mA}$			0.55	V
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		30		pF
Reverse recovery time <sup>*</sup>	$t_{rr}$	$I_F = I_R = 100 \text{ mA}$ $I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$		3		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 1 000 MHz

3. \* :  $t_{rr}$  measuring instrument



Marking Symbol: M3C

Internal Connection

